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AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1 to 21 (Cancelled)

22. (New) Circuitry comprising:

a terminal for use with a high-frequency signal;

at least two signal lines;

a switching unit for connecting the terminal to a signal line; and

a primary protection device for protecting against electrostatic discharges, the primary protection device being between the terminal and the switching unit, the primary protection device comprising a first element that diverts voltages having a pulse height greater than 200V to a reference potential.

23. (New) The circuitry of claim 22, wherein the first element has an insertion attenuation that is less than 0.3 dB.

24. (New) The circuitry of claim 22, wherein the first element has a capacitance that is less than 1 pF.

25. (New) The circuitry of claim 22, wherein the first element comprises a gallium arsenide double diode.

26. (New) The circuitry claim 22, wherein the primary protection device comprises a circuit path that connects the terminal and the switching unit; and wherein the first element connects the circuit path to the reference potential.

27. (New) The circuitry of claim 22, further comprising:  
a second element that is in parallel with the first element, the second element for limiting a current load of the first element.

28. (New) The circuitry of claim 27, further comprising:  
a capacitor on a circuit path between the first element and the second element

29. (New) The circuitry of claim 27, wherein the second element comprises is a discharger.

30. (New) The circuitry of claim 27, wherein the second element comprises a polymer suppressor.

31. (New) The circuitry of claim 27, wherein the second element comprises an over-voltage component having a capacitance that is less than 1 pF.

32. (New) The circuitry of claim 27, wherein the second element comprises an inductive element having an inductance that is greater than 18 nH.

33. (New) The circuitry of claim 22, further comprising:  
circuit paths that provide control signals to the switching unit, each of the circuit paths comprising a secondary protection device for protecting against electrostatic discharges.

34. (New) The circuitry of claim 22, further comprising:  
a circuit path for supplying for an operating voltage to the switching unit, the circuit path comprising a secondary protection device for protecting against electrostatic discharges.

35. (New) The circuitry of claim 22, wherein the switching unit comprises field effect transistors, a contact break distance of each of the field effect transistors connecting the terminal to a signal line; and

wherein the circuitry further comprises:

circuit paths that connect to gates of the field effect transistors, the circuit paths for providing control signals to the gates, each of the circuit paths comprising a secondary protection device for protecting against electrostatic discharges.

36. (New) The circuitry of claims 33 to 35,  
wherein the secondary protection device comprises a voltage-limiting element  
having a switching voltage that is less than 100 V.

37. (New) The circuitry of claim 36, wherein the voltage-limiting element  
comprises a varistor.

38. (New) The circuitry of claim 36, wherein the voltage-limiting element  
comprises a Zener diode.

39. (New) The circuitry of claim 35, wherein at least one secondary protection  
device is connected to the reference potential.

40. (New) The circuitry of claim 22, wherein the switching unit comprises PIN  
diodes.

41. (New) The circuitry of claim 22, wherein the switching unit comprises a  
gallium arsenide switch.

42. (New) The circuitry of claim 22, wherein the terminal comprises an antenna  
input of a mobile telephone.

43. (New) The circuitry of claim 22, wherein the signal lines comprises transmitting and receiving paths of a mobile telephone.

44. (New) The circuitry of claim 22, wherein the switching unit and the primary protection device are integrated into a multi-layer ceramic substrate.